## 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPAK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

#### 2. Features and benefits

- · Fully automotive qualified to beyond AEC-Q101:
  - -55 °C to +175 °C rating suitable for thermally demanding environments
- LFPAK88 package
  - Designed for smaller footprint and improved power density over older wire bond packages such as D<sup>2</sup>PAK for today's space constrained high power automotive applications
  - Thin package and copper clip enables LFPAK88 to be highly efficient thermally
- LFPAK copper clip technology enabling improvements over wire bond packages by:
  - Increased maximum current capability and excellent current spreading
  - Improved R<sub>DSon</sub>
  - · Low source inductance
  - Low thermal resistance R<sub>th</sub>
- LFPAK Gull Wing leads:
  - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - · Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
  - Reduced cell pitch and superjunction platform enables lower R<sub>DSon</sub> in the same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight V<sub>GS(th)</sub> limits enable easy paralleling of MOSFETs

# 3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- LED lighting
- · Ultra high performance power switching

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	300	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	294	W	



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; Fig. 11		0.74	1.06	1.2	mΩ
Dynamic ch	naracteristics						
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14		-	14	28	nC
Source-dra	in diode						
Q <sub>r</sub>	recovered charge	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V	[2]	-	38	-	nC
S	softness factor	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C		-	0.82	-	

<sup>[1] 300</sup>A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating emperature.

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	S	source		G—(F)
4	S	source		mbb076 S
mb	D	mounting base; connected to drain	LFPAK88 (SOT1235)	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
BUK7S1R2-40H	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235			

# 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
BUK7S1R2-40H	7S1R240H

<sup>[2]</sup> includes capacitive recovery

## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	294	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	300	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3		-	1341	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	1 diode			'		
Is	source current	T <sub>mb</sub> = 25 °C	[2]	-	294	Α
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	1341	Α
Avalanche ru	uggedness		'	_	'	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 120 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	277	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 40 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega; Fig. 4$	[5]	-	199	А

- [1] 300A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating emperature.
- [2] 294A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature.
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.
- [5] Protected by 100% test.

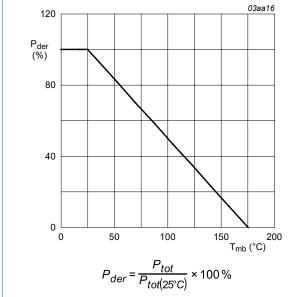
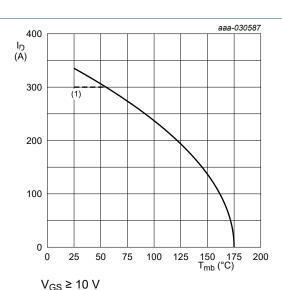


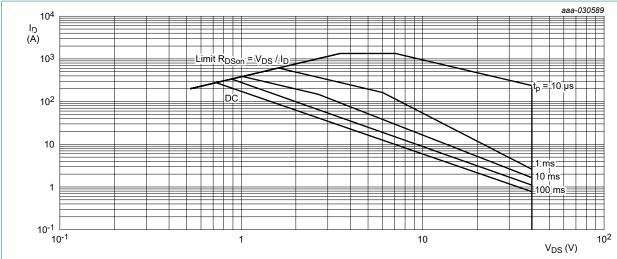
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



(1) 300A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

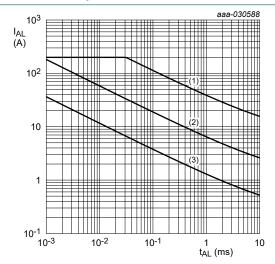
Fig. 2. Continuous drain current as a function of mounting base temperature

## N-channel 40 V, 1.2 m $\Omega$ standard level MOSFET in LFPAK88



T<sub>mb</sub> = 25 °C; I<sub>DM</sub> is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1)  $T_{j \text{ (init)}}$  = 25 °C; (2)  $T_{j \text{ (init)}}$  = 150 °C; (3) Repetitive Avalanche

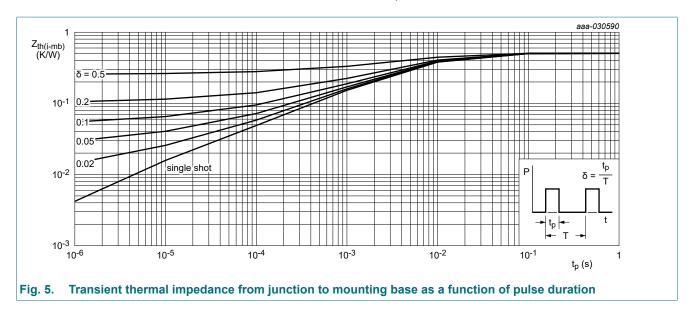
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.45	0.51	K/W

### N-channel 40 V, 1.2 m $\Omega$ standard level MOSFET in LFPAK88



## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	43	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -40 °C	-	40.5	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	40	-	V
V <sub>GS(th)</sub>	gate-source threshold $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fi$ voltage $Fig. 10$	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9; Fig. 10$	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$	-	-	4.3	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.06	1.2	μΑ
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	1.6	25	μΑ
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	180	500	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 11	0.74	1.06	1.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; Fig. 12	1.05	1.59	1.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 12	1.16	1.76	2.1	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	1.46	2.21	2.6	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.4	1.05	2.6	Ω
Dynamic ch	naracteristics		'	'	'	1
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	80	112	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	22	33	nC
$Q_{GD}$	gate-drain charge	7	-	14	28	nC

### N-channel 40 V, 1.2 m $\Omega$ standard level MOSFET in LFPAK88

Parameter	Conditions		Min	Тур	Max	Unit
input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		-	6014	8420	pF
output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	1352	1893	pF
reverse transfer capacitance			-	244	537	pF
turn-on delay time	$V_{DS} = 30 \text{ V}; R_{L} = 1.2 \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \Omega$		-	19	-	ns
rise time			-	16	-	ns
turn-off delay time			-	50	-	ns
fall time	1		-	22	-	ns
ain diode	,					'
source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.77	1	V
reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	39	-	ns
recovered charge	V <sub>DS</sub> = 20 V	[1]	-	38	-	nC
softness factor	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C		-	0.82	-	
	$I_S$ = 25 A; $dI_S/dt$ = -500 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_i$ = 25 °C		-	0.73	-	
	input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time source-drain voltage reverse recovery time recovered charge	$\begin{array}{ll} \text{input capacitance} \\ \text{output capacitance} \\ \text{reverse transfer} \\ \text{capacitance} \\ \text{turn-on delay time} \\ \text{turn-off delay time} \\ \text{fall time} \\ \\ \\ \text{In diode} \\ \\ \text{source-drain voltage} \\ \text{reverse recovery time} \\ \text{recovered charge} \\ \\ \text{softness factor} \\ \\ \\ \\ \text{In diode} \\ \\ In$	input capacitance output capacitance output capacitance $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ Fig. 15}$ $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$ rise time $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$ rise time $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \Omega$ $V_{DS} = 10 \text{ V};$ $R_{G(ext)} = 10 $	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

#### [1] includes capacitive recovery

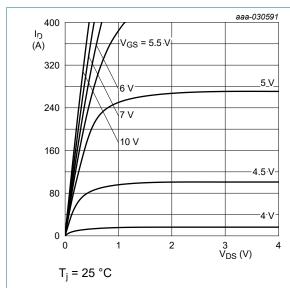


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

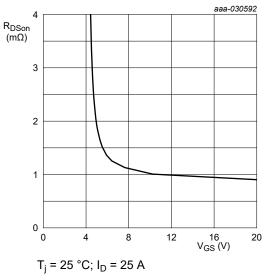


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### N-channel 40 V, 1.2 m $\Omega$ standard level MOSFET in LFPAK88

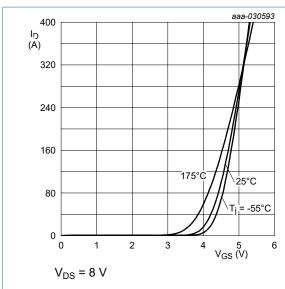


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

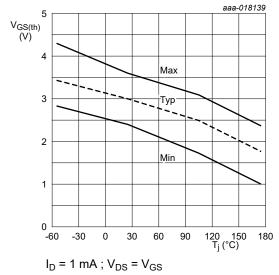


Fig. 10. Gate-source threshold voltage as a function of junction temperature

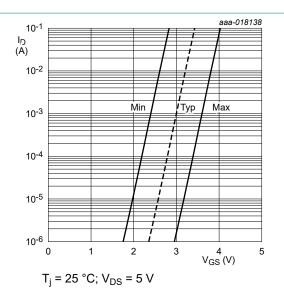


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

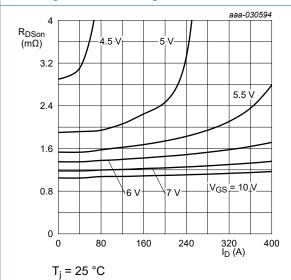


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

### N-channel 40 V, 1.2 m $\Omega$ standard level MOSFET in LFPAK88

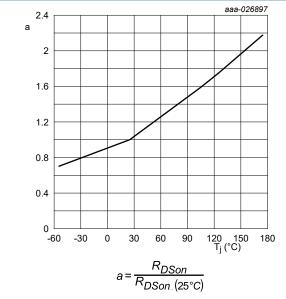


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

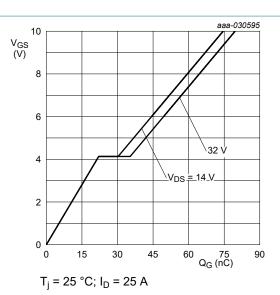


Fig. 13. Gate-source voltage as a function of gate charge; typical values

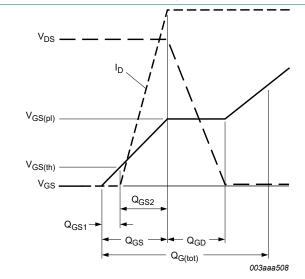
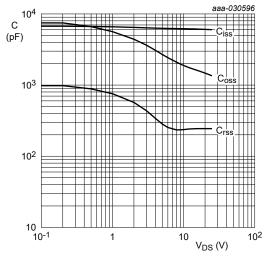


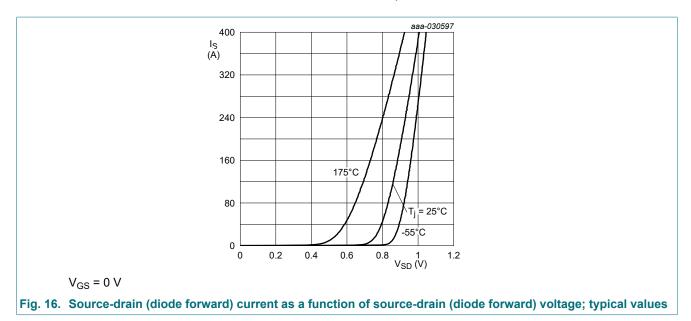
Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### N-channel 40 V, 1.2 m $\Omega$ standard level MOSFET in LFPAK88



# 11. Package outline

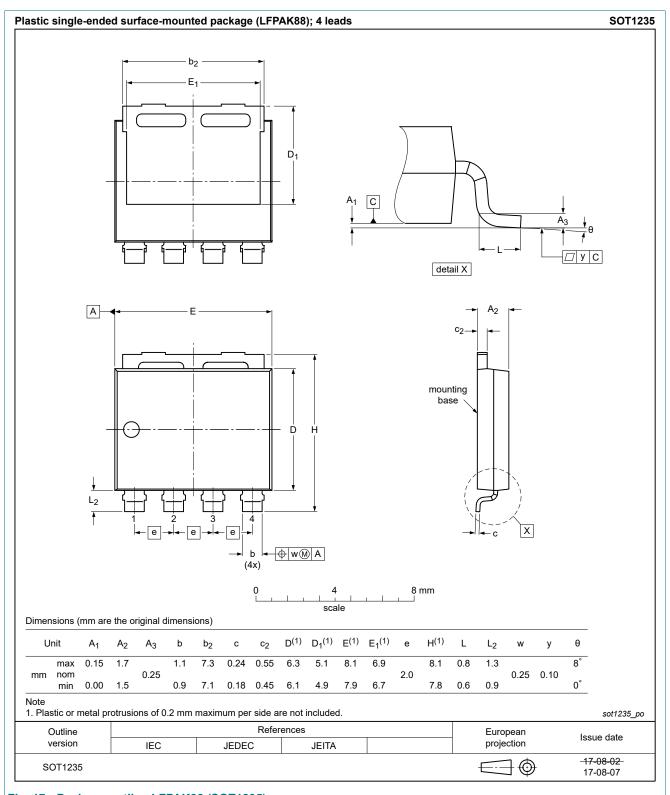
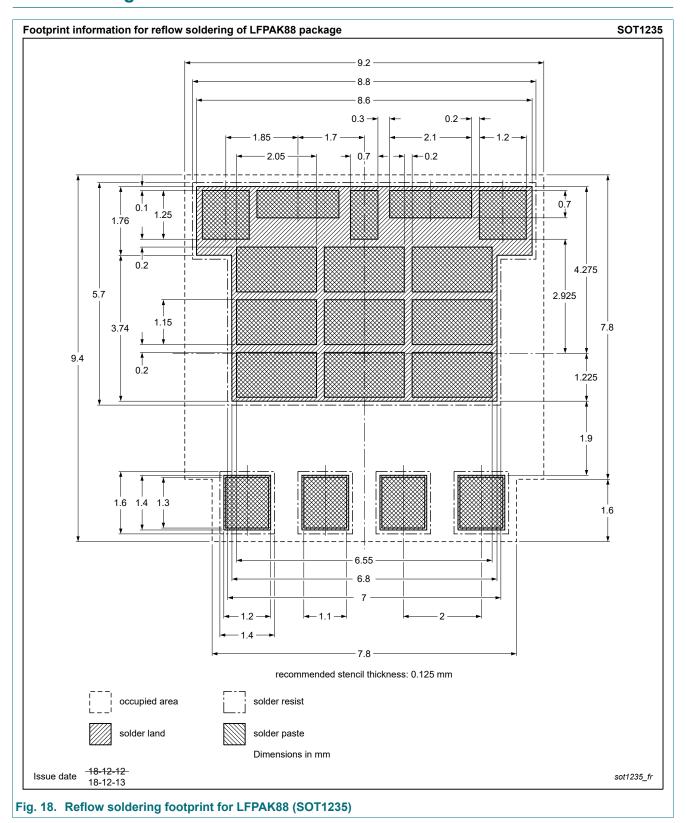


Fig. 17. Package outline LFPAK88 (SOT1235)

# 12. Soldering



## 13. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B
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